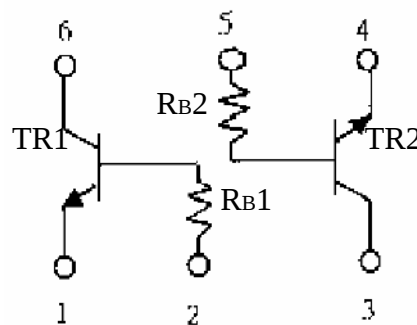


Dual NPN Digital Transistors

Features:

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- Two KWBC143T chips in a SOT-363 package.
- Mounting by SOT-323 automatic mounting machines is possible.
- Mounting cost and area can be cut in half.
- Transistor elements are independent, eliminating interference.
- Complements the KWBA143T.
- Pb-free package.

SOT-363R



$$RB1=4.7k\Omega, RB2=4.7k\Omega$$

Absolute Maximum Ratings (Each Transistor, TA=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	100	mA
Power Dissipation(per device)	P _d	200 (Note)	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : 150mW per element must not be exceeded.

Electrical Characteristics (Each Transistor, TA=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	V _{CB0}	50	-	-	V	I _C =50μA
Collector-Emitter Breakdown Voltage	V _{CEO}	50	-	-	V	I _C =1mA
Emitter-Base Breakdown Voltage	V _{EB0}	5	-	-	V	I _E =50μA
Collector-Base Cutoff Current	I _{CB0}	-	-	0.5	μA	V _{CB} =50V
Emitter-Base Cutoff Current	I _{EB0}	-	-	0.5	μA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-	0.3	V	I _C =5mA, I _B =0.25mA
DC Current Gain	h _{FE}	100	-	600	-	V _{CE} =5V, I _C =1mA
Input Resistance	R	3.29	4.7	6.11	kΩ	-
Transition Frequency	f _T	-	250	-	MHz	V _{CE} =10V, I _C =5mA, f =100MHz *

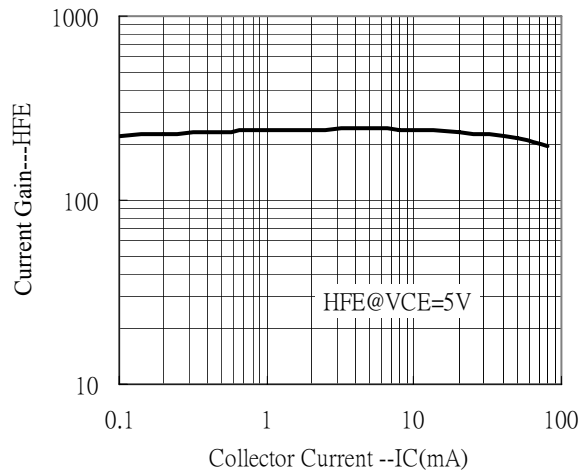
* Transition frequency of the device

Ordering Information

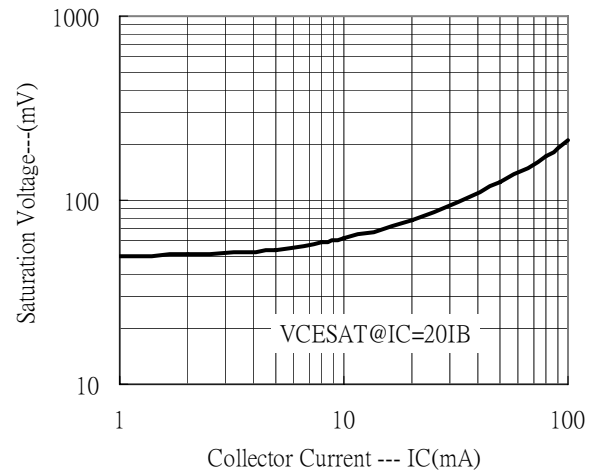
Device	Package	Shipping	Marking
KWBC143T	SOT-363 (Pb-free)	3000 pcs / Tape & Reel	7F

Characteristic Curves

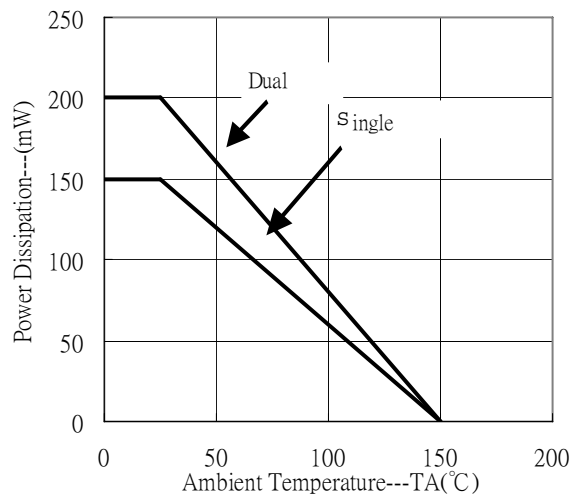
Current Gain vs Collector Current



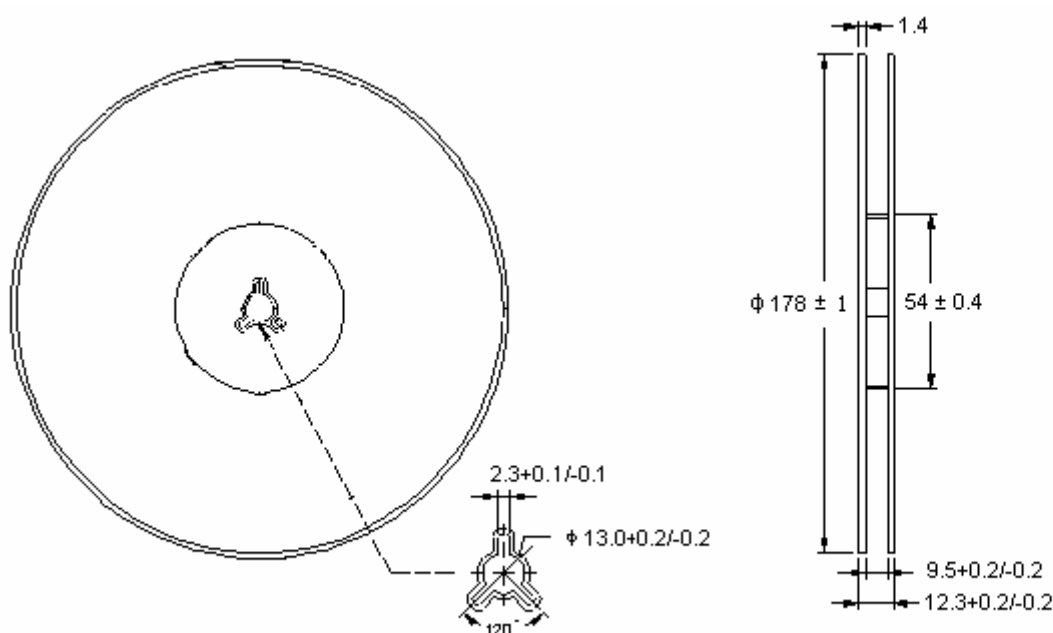
Saturation Voltage vs Collector Current



Power Derating Curves

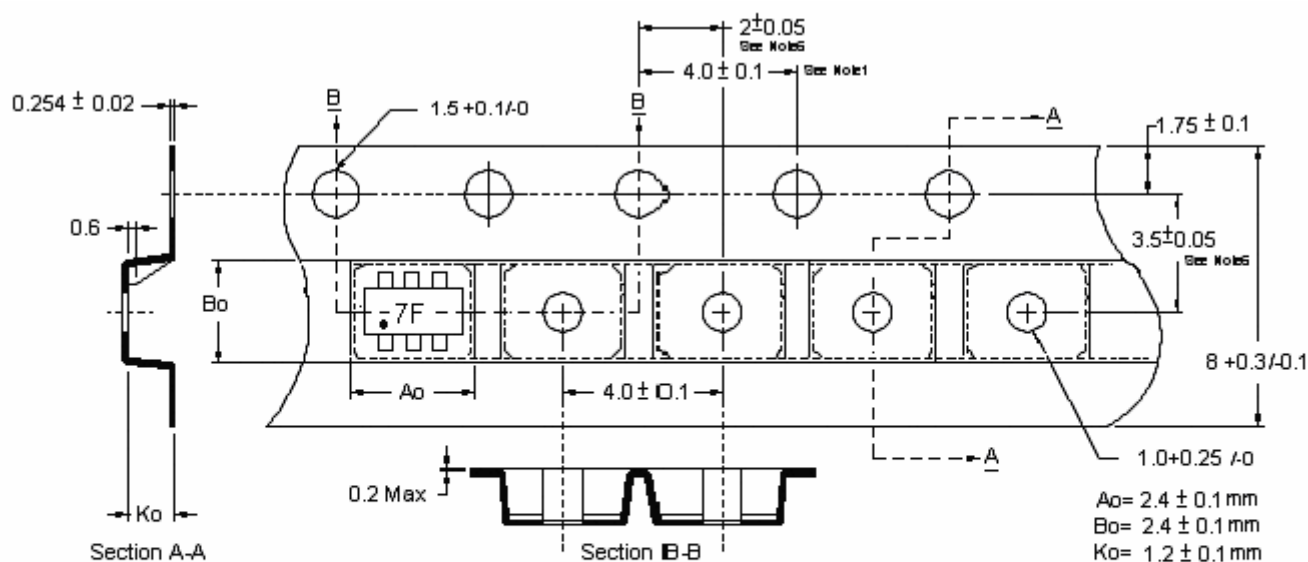


Reel Dimension



Unit: millimeter

Carrier Tape Dimension

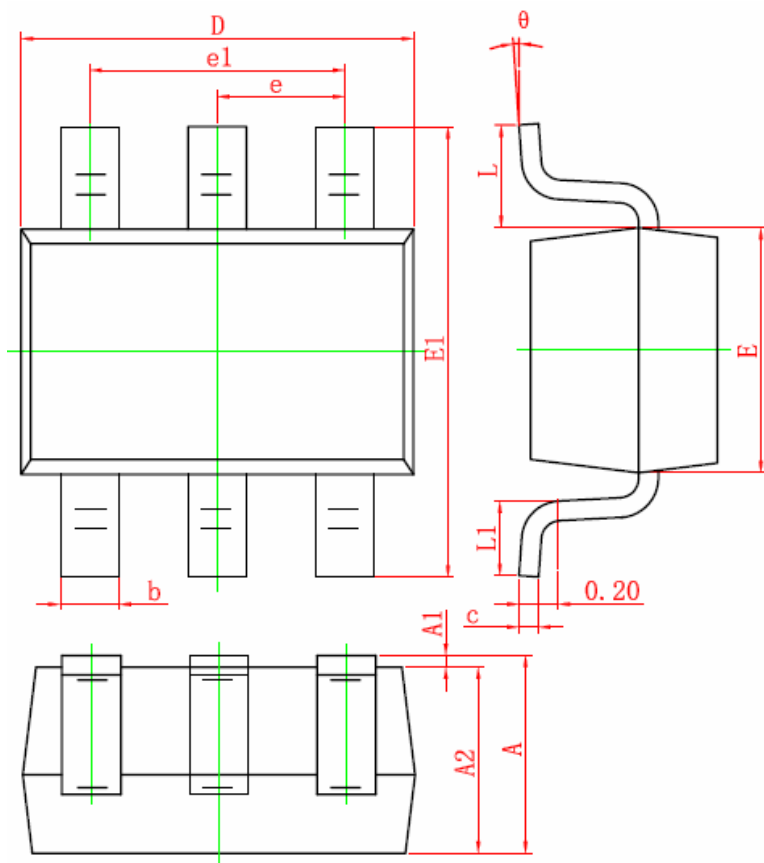


Notes

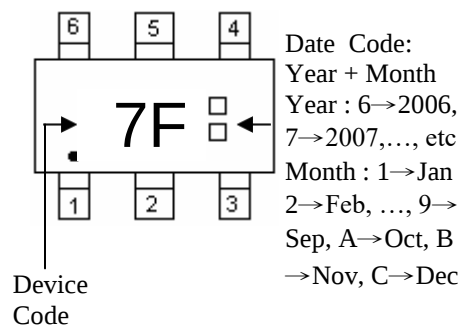
1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material: Conductive Black Polystyrene.
4. A_0 & B_0 measured on a plane 0.3mm above the bottom of the pocket.
5. K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

SOT-363 Dimension



Marking:



6-Lead SOT-363R Plastic Surface Mounted Package

Style:

Pin 1. Emitter1 (E1)
 Pin 2. Base1 (B1)
 Pin 3. Collector2 (C2)
 Pin 4. Emitter2 (E2)
 Pin 5. Base2 (B2)
 Pin 6. Collector1 (C1)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					